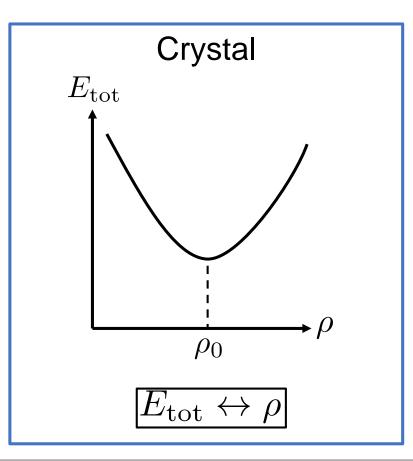
A novel method to predict densities of amorphous materials from first-principles calculations

Yoritaka Furukawa and Yu-ichiro Matsushita Oshiyama group Department of Applied Physics ,The University of Tokyo

(arxiv:1704.06107)

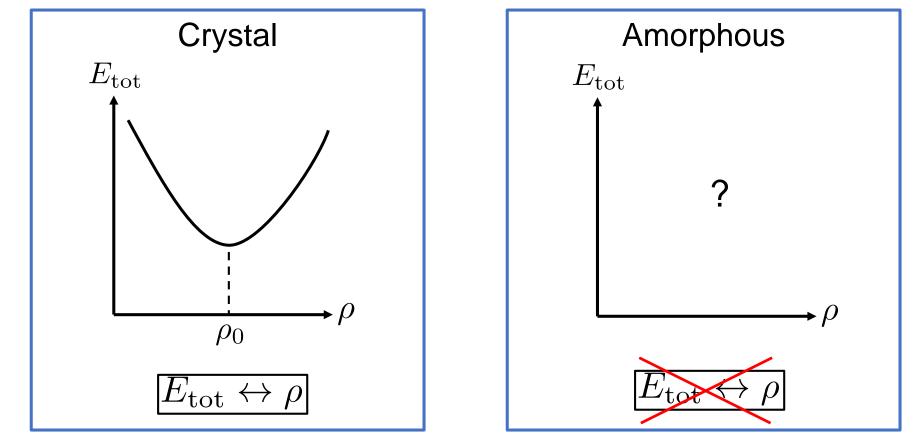
Determining the densities of materials

The densities (ρ) of crystalline materials are determined by calculating the total energy (E_{tot}), since E_{tot} corresponds to ρ



Determining the densities of materials

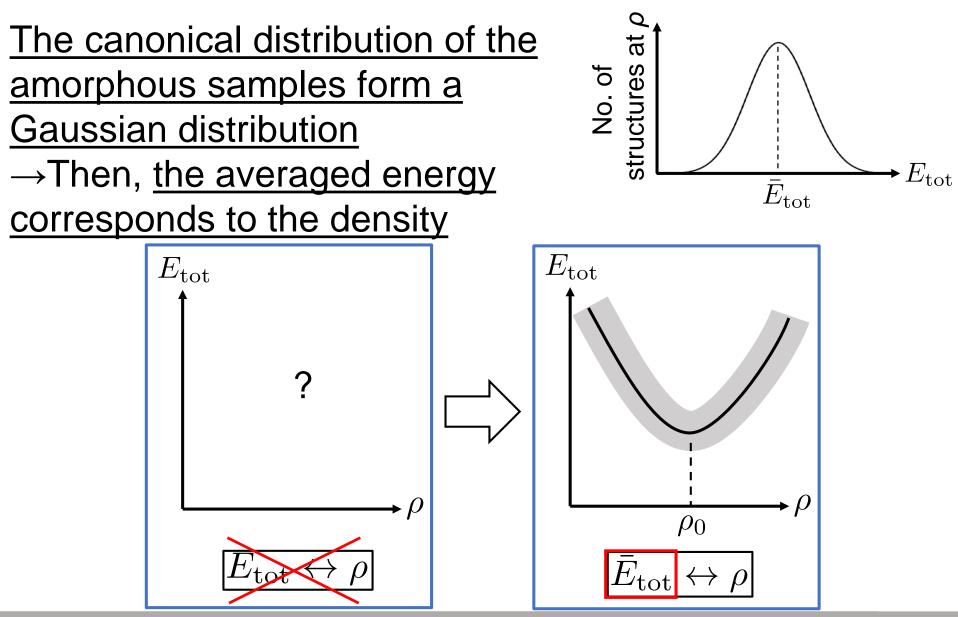
Not for amorphous materials, because the structures are disordered



Any solution for amorphous materials? \rightarrow our work

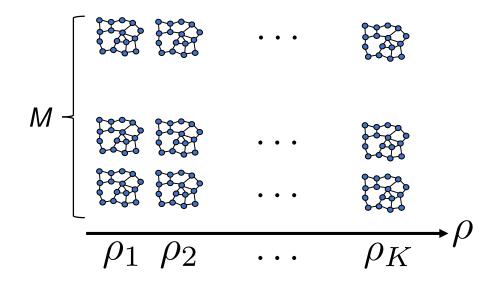
iDFT @RIKEN 2017

An assumption

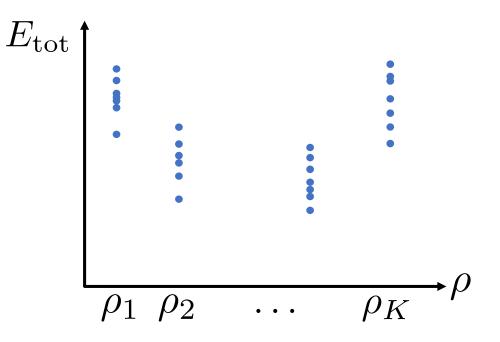


- 1. Generate multiple samples (1,...,M) at different densities $(\rho_1,...,\rho_K)$
- 2. Obtain their total energies from DFT
- 3. Average the total energies at each density
- 4. Find the density that minimizes the average $\rightarrow \rho_0$

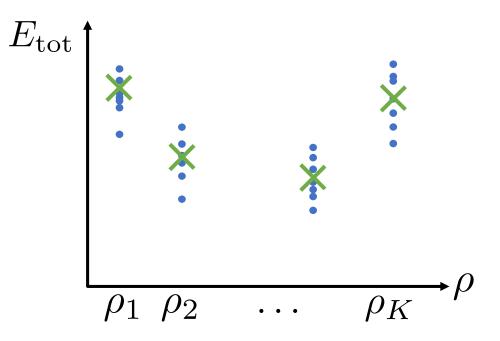
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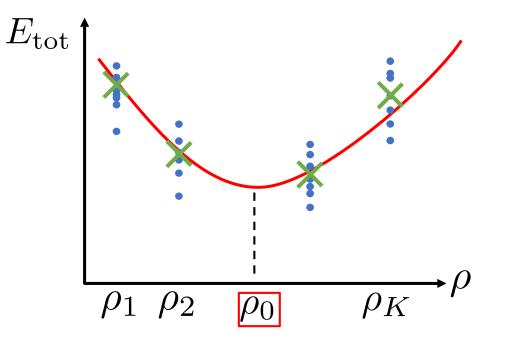
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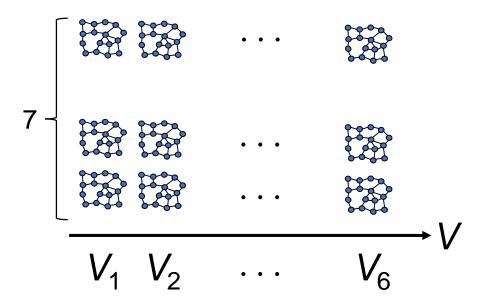


 \rightarrow examined with amorphous Si (a-Si)

Generating a-Si samples

1. Generate 7 samples at 6 different volumes V

- $V/V_{\rm C}$ = 0.86 1.16 ($V_{\rm C}$: volume of crystal)
- System: 54 Si atoms/cell with periodic boundaries

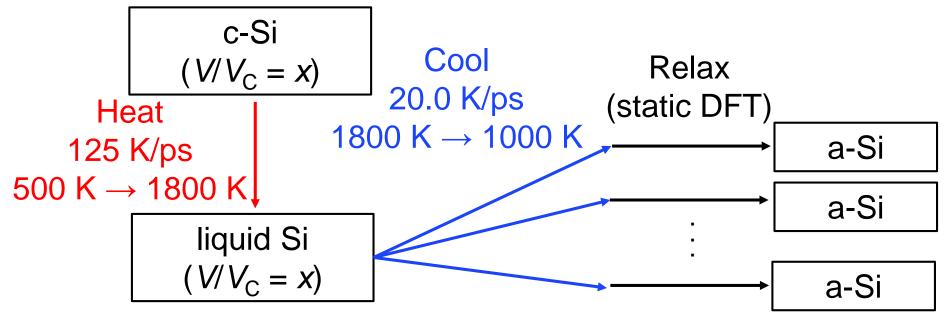


Generating a-Si samples

1. Generate 7 samples at 6 different volumes V

- $V/V_{\rm C} = 0.86 1.16$ ($V_{\rm C}$: volume of crystal)
- System: 54 Si atoms/cell with periodic boundaries
- Melt-quench method by <u>Car-Parrinello molecular</u> <u>dynamics (CPMD)</u>

(functional=PBE, cutoff=40 Ry, BZ sampling=Γ point)

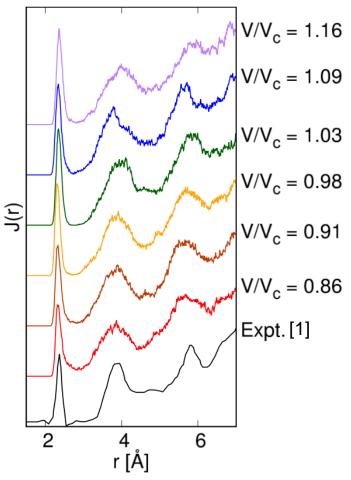


Radial distributions of samples

Good agreement with experiments:

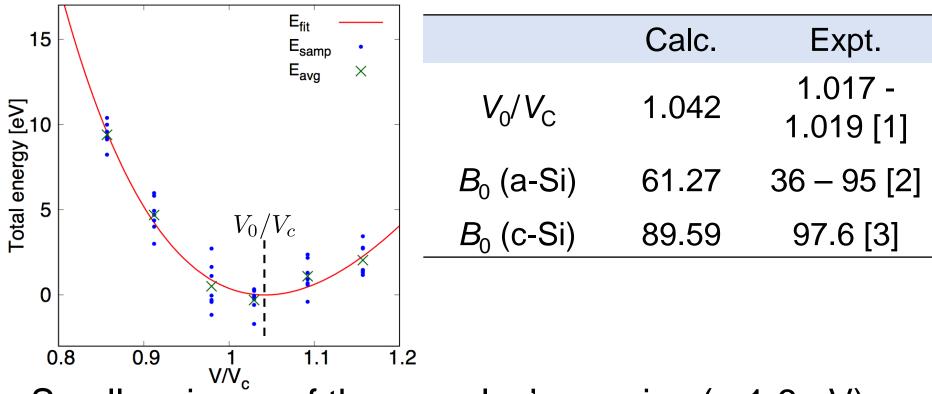
- First peak at ~2.3 Å
- Broader peaks subsequently

 \rightarrow Obtained samples are certainly valid a-Si



[1] PRB 60, 19 (1999)

Total energies



- Small variance of the samples' energies (< 1.6 eV)

- Both V_0/V_C and B_0 (bulk modulus) agrees with expt. \rightarrow Our method works for a-Si

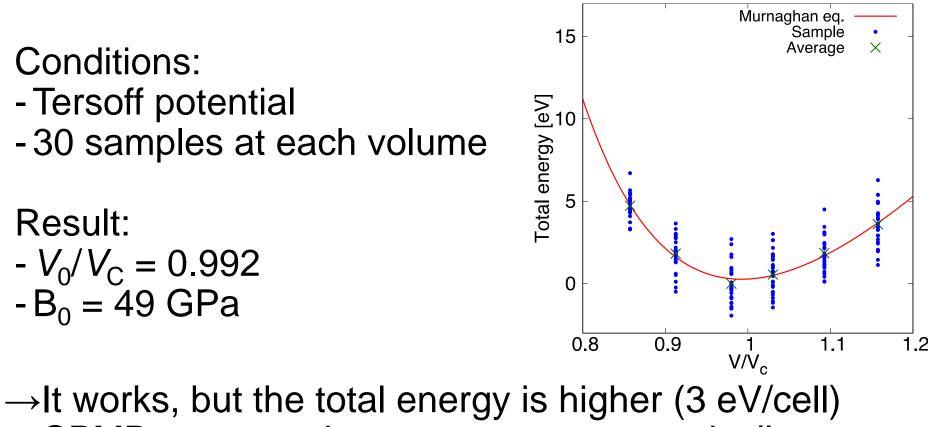
[1] Appl. Phys. Lett. 64, 437 (1994)

[2] "Thin film materials", Cambridge University Press, (2003); PRB 58, 8941 (1998)

[3] J. Microelectromech. Syst. 19, 2 (2010)

Results from MD simulations

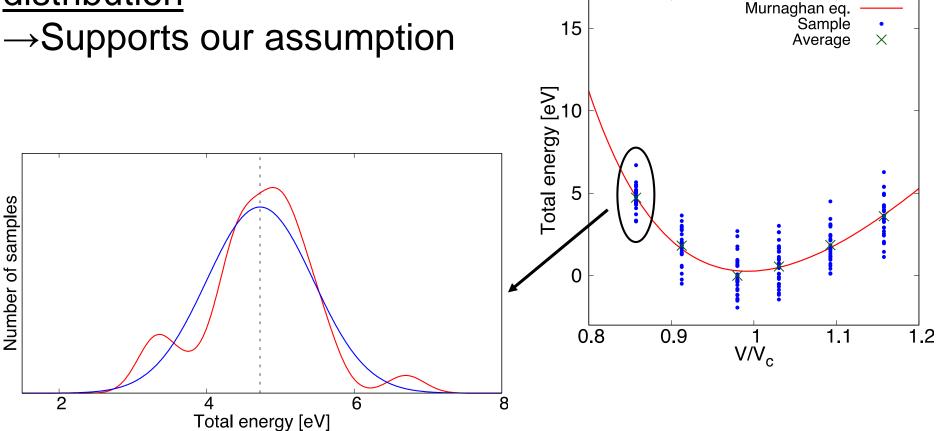
What if we generate samples by MD instead of CPMD?



 \rightarrow It works, but the total energy is higher (3 eV/cell) \rightarrow <u>CPMD-generated structures are energetically</u> <u>preferable</u>

Results from MD simulations

A finding: the sample distribution is close to Gaussian distribution



Summary

- A method to computationally determine the density of amorphous materials is proposed
- For a-Si, both the density (volume) and the bulk modulus have been well reproduced
- Results from MD simulations imply the validity of our underlying assumption

